# Hex Schmitt-Trigger Inverter with LSTTL Compatible Inputs

# High–Performance Silicon–Gate CMOS

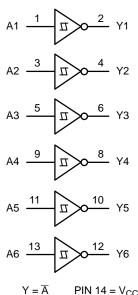
The MC74HCT14A may be used as a level converter for interfacing TTL or NMOS outputs to high–speed CMOS inputs.

The HCT14A is useful to "square up" slow input rise and fall times. Due to the hysteresis voltage of the Schmitt trigger, the HCT14A finds applications in noisy environments.

#### Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

LOGIC DIAGRAM



# PIN 7 = GND



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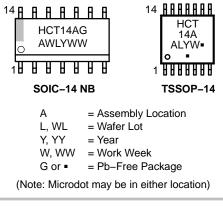
D SUFFIX CASE 751A

TSSOP-14 DT SUFFIX CASE 948G

#### **PIN ASSIGNMENT**

A1 [	1●		l v <sub>cc</sub>
Y1 [	2	13	] A6
A2 [	3	12	] Y6
Y2 [	4	11	] A5
A3 [	5	10	] Y5
Y3 [	6	9	] A4
GND [	7	8	] Y4

#### MARKING DIAGRAMS



#### FUNCTION TABLE

Input A	Output Y
L	н
н	L

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### MAXIMUM RATINGS

Symbol	F	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	(Referenced to GND)	-0.5 to +7.0	V
VI	DC Input Voltage	(Referenced to GND)	–0.5 to V <sub>CC</sub> + 0.5	V
Vo	DC Output Voltage	(Referenced to GND)	–0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
I <sub>OK</sub>	DC Output Diode Current		±25	mA
Ι <sub>Ο</sub>	DC Output Sink Current		±25	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±50	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for	or 10 Seconds	260	°C
Τ <sub>J</sub>	Junction Temperature under Bias		+150	°C
$\theta_{JA}$	Thermal Resistance	SOIC TSSOP	125 170	°C/W
PD	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V–0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 4000 > 300 > 1000	V
I <sub>Latchup</sub>	Latchup Performance	Above $V_{CC}$ and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Tested to EIA/JESD22–A114–A.

2. Tested to EIA/JESD22-A115-A.

3. Tested to JESD22-C101-A.

4. Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced	to GND)	4.5	5.5	V
V <sub>I</sub> , V <sub>O</sub>	DC Input Voltage, Output Voltage (Referenced	to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)		-	(Note 5)	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability. 5. No Limit when  $V_I \approx 50\% V_{CC}$ ,  $I_{CC} > 1 \text{ mA}$ .

6. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

					Ten	nperatu	ıre Limi	t		
			v <sub>cc</sub>	−55°C	to 25°C	≤8	5°C	≤12	25°C	1
Symbol	Parameter	Test Conditions	Volts	Min	Max	Min	Max	Min	Max	Unit
V <sub>T+</sub> max	Maximum Positive–Going Input Threshold Voltage	$\begin{array}{l} V_{O} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\  I_{out}  \leq 20 \ \mu A \end{array}$	4.5 5.5		1.9 2.1		1.9 2.1		1.9 2.1	V
$V_{T+}$ min	Minimum Positive–Going Input Threshold Voltage	$\begin{array}{l} V_{O} = 0.1 \ V \ or \ V_{CC} - 0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array} \end{array} \label{eq:VC}$	4.5 5.5	1.2 1.4		1.2 1.4		1.2 1.4		V
V <sub>T-</sub> max	Maximum Negative–Going Input Threshold Voltage	$\begin{array}{l} V_{O}=0.1 \ V \ or \ V_{CC}-0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array} \end{array} \label{eq:VC}$	4.5 5.5		1.2 1.4		1.2 1.4		1.2 1.4	
$V_{T-}min$	Minimum Negative–Going Input Threshold Voltage	$\begin{array}{l} V_{O}=0.1 \ V \ or \ V_{CC}-0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array} \end{array} \label{eq:VC}$	4.5 5.5	0.5 0.6		0.5 0.6		0.5 0.6		
V <sub>H</sub> max	Maximum Hysteresis Voltage	$\begin{array}{l} V_{O}=0.1 \ V \ or \ V_{CC}-0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array} \end{array} \label{eq:VC}$	4.5 5.5		1.4 1.5		1.4 1.5		1.4 1.5	
V <sub>H</sub> min	Minimum Hysteresis Voltage	$\begin{array}{l} V_{O}=0.1 \ V \ or \ V_{CC}-0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array} \end{array} \label{eq:VC}$	4.5 5.5	0.4 0.4		0.4 0.4		0.4 0 4		
V <sub>OH</sub>	Minimum High–Level Output Voltage	$V_{I} < V_{T-}$ min $ I_{out}  \le 20 \ \mu A$	4.5 5.5	4.4 5.4		4.4 5.4		4.4 5.4		V
		$V_l < V_T - min$ $ I_{out}  \le 4.0 mA$	4.5	3.98		3.84		3.7		
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$ \begin{array}{l} V_l \geq V_{T+} \max \\  I_{out}  \leq 20 \ \mu A \end{array} $	4.5 5.5		0.1 0.1		0.1 0.1		0.1 0.1	V
		$V_l \ge V_{T+} max$ $ I_{out}  \le 4.0 mA$	4.5		0.26		0.33		0.4	
Ι <sub>ΙΚ</sub>	Maximum Input Leakage Current	$V_1 = V_{CC}$ or GND	5.5		±0.1		±1.0		±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per package)	$V_I = V_{CC}$ or GND $I_{out} = 0 \ \mu A$	5.5		1.0		10		40	μΑ
			≥ - 55°C 25		<b>25</b> °	C to 12	5°C			
$\Delta I_{CC}$	Additional Quiescent Supply Current	$V_1 = 2.4 V$ , Any One Input $V_1 = V_{CC}$ or GND, Other Inputs $I_{out} = 0 \mu A$	5.5		2.9			2.4		mA

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ ; Input $t_r = t_f = 6.0 \text{ ns}$ )

				Guaranteed Limit						
				−55°C	to 25°C	≤8	5°C	≤12	25°C	
Symbol	Parameter	Test Conditions	Figures	Min	Max	Min	Max	Min	Мах	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (L to H)	$V_{CC} = 5.0 \text{ V} \pm 10\%$ $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$	1&2		32		40		48	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output	$V_{CC} = 5.0 \text{ V} \pm 10\%$ $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$	1&2		15		19		22	ns
				Typical @ 25°C, V <sub>CC</sub> = 5.0 V						

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V		ł
C <sub>PD</sub>	Power Dissipation Capacitance, per Inverter (Note 7)	32	pF	
	determine the net lead dynamic network constraints $\mathbf{D} = \mathbf{C} + \frac{2t}{2t}$			

7. Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

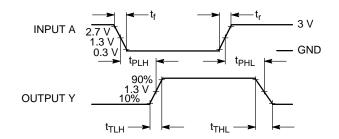
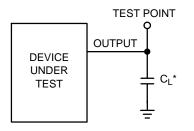


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance.

Figure 2. Test Circuit

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCT14ADG	SOIC-14 NB	55 Units / Rail
NLV74HCT14ADG*	(Pb-Free)	55 Units / Rail
MC74HCT14ADR2G	SOIC-14 NB	2500 / Tana & Real
NLV74HCT14ADR2G*	(Pb-Free)	2500 / Tape & Reel
MC74HCT14ADTR2G	TSSOP-14	2500 / Tape & Reel
NLV74HCT14ADTR2G*	(Pb-Free)	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

# DUSEU

0.068

0.019

0.344

0.244



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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#### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON CATHODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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